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Si570/Si571



10 MHz to 1.4 GHz I²C Programmable XO/VCXO

Features

- Any programmable output frequencies from 10 to 945 MHz and select frequencies to 1.4 GHz
- I²C serial interface
- 3rd generation DSPLL[®] with superior jitter performance
- 3x better frequency stability than SAW-based oscillators

Applications

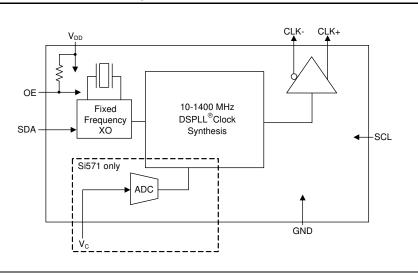
- SONET/SDH
- xDSL
- 10 GbE LAN/WAN
- ATE

- Internal fixed crystal frequency ensures high reliability and low aging
- Available LVPECL, CMOS, LVDS, and CML outputs
- Industry-standard 5x7 mm package
- Pb-free/RoHS-compliant
- 1.8, 2.5, or 3.3 V supply
- High performance instrumentation
- Low-jitter clock generation
- Optical modules
- Clock and data recovery

Description

The Si570 XO/Si571 VCXO utilizes Silicon Laboratories' advanced DSPLL[®] circuitry to provide a low-jitter clock at any frequency. The Si570/Si571 are userprogrammable to any output frequency from 10 to 945 MHz and select frequencies to 1400 MHz with <1 ppb resolution. The device is programmed via an I²C serial interface. Unlike traditional XO/VCXOs where a different crystal is required for each output frequency, the Si57x uses one fixed-frequency crystal and a DSPLL clock synthesis IC to provide any-frequency operation. This IC-based approach allows the crystal resonator to provide exceptional frequency stability and reliability. In addition, DSPLL clock synthesis provides superior supply noise rejection, simplifying the task of generating low-jitter clocks in noisy environments typically found in communication systems.

Functional Block Diagram





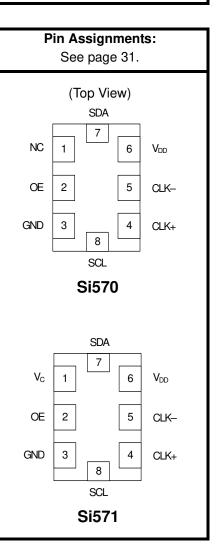




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1. Detailed Block Diagrams

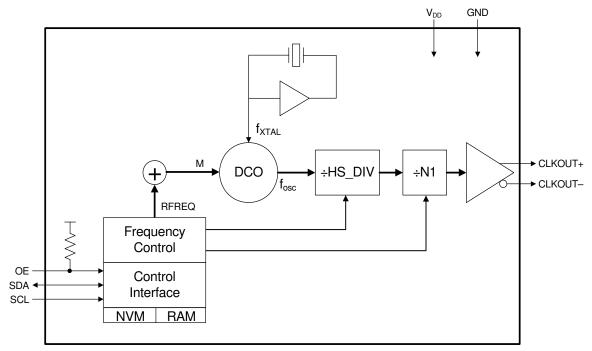


Figure 1. Si570 Detailed Block Diagram

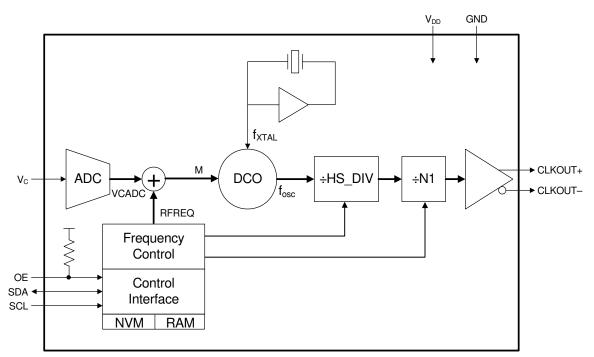


Figure 2. Si571 Detailed Block Diagram



2. Electrical Specifications

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
		3.3 V option	2.97	3.3	3.63	
Supply Voltage ¹	V_{DD}	2.5 V option	2.25	2.5	2.75	V
		1.8 V option	1.71	1.8	1.89	-
Supply Current	I _{DD}	Output enabled LVPECL CML LVDS CMOS TriState mode	 	120 108 99 90 60	130 117 108 98 75	mA
Output Enable (OE) ² , Serial Data (SDA), Serial Clock (SCL)		V _{IH} V _{IL}	0.75 x V _{DD}	_	— 0.5	v
Operating Temperature Range	T _A		-40		85	°C
Notes: 1. Selectable parameter specifie	d by part num	nber. See Section "7. Ord	ering Information	n" on page 3	32 for further	details.

Table 1. Recommended Operating Conditions

2. OE pin includes a 17 k Ω pullup resistor to V_DD. See "7.Ordering Information".

Table 2. V_C Control Voltage Input (Si571)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Control Voltage Tuning Slope ^{1,2,3}	κ _v	V_{C} 10 to 90% of V_{DD}	_	33 45 90 135 180 356	_	ppm/V
Control Voltage Linearity ⁴	L _{VC}	BSL	-5	±1	+5	%
Control Voltage Linearity		Incremental	-10	±5	+10	/0
Modulation Bandwidth	BW		9.3	10.0	10.7	kHz
V _C Input Impedance	Z _{VC}		500	—		kΩ
Nominal Control Voltage ⁵	V _{CNOM}	@ f _O	—	V _{DD} /2		V
Control Voltage Tuning Range	V _C		0		V _{DD}	V

Notes:

1. Positive slope; selectable option by part number. See "7. Ordering Information" on page 32.

2. For best jitter and phase noise performance, always choose the smallest Ky that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (K_V), Stability, and Absolute Pull Range (APR)" for more information. **3.** K_V variation is ±10% of typical values.

4. BSL determined from deviation from best straight line fit with V_C ranging from 10 to 90% of V_{DD}. Incremental slope is determined with V_C ranging from 10 to 90% of V_{DD}. 5. Nominal output frequency set by V_{CNOM} = $1/2 \times V_{DD}$.



Table 3. CLK± Output Frequency Characteristics

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Programmable Frequency	f	LVPECL/LVDS/CML	10		1417.5	
Range ^{1,2}	f _O	CMOS	10		160	MHz
Temperature Stability ^{1,3}		T _A = −40 to +85 ^o C	-7 -20 -50 -100		7 +20 +50 +100	ppm
Initial Accuracy				1.5	+100	ppm
Aging	4	Frequency drift over first year			±3	ppm
	f _a	Frequency drift over 20-year life			±10	ppm
		Temp stability = ±7 ppm	_		±20	ppm
Total Stability		Temp stability = ±20 ppm	_		±31.5	ppm
		Temp stability = ±50 ppm	_		±61.5	ppm
Absolute Pull Range ^{1,3}	APR		±12	_	±375	ppm
Power up Time ⁴	t _{OSC}		—		10	ms
Notes: 1. See Section "7. Ordering Ir 2. Specified at time of order b		n page 32 for further details.				

 Specified at time of order by part number. Three speed grades available: Grade A covers 10 to 945 MHz, 970 to 1134 MHz, and 1213 to 1417.5 MHz. Grade B covers 10 to 810 MHz. Grade C covers 10 to 280 MHz.

- 3. Selectable parameter specified by part number.
- 4. Time from power up or tristate mode to $f_{\mbox{O}}.$



Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
	Vo	mid-level	V _{DD} – 1.42	—	V _{DD} – 1.25	V
LVPECL Output Option ¹	V _{OD}	swing (diff)	1.1	—	1.9	V _{PP}
	V _{SE}	swing (single-ended)	0.55	_	0.95	V_{PP}
LVDS Output Option ²	Vo	mid-level	1.125	1.20	1.275	V
	V _{OD}	swing (diff)	0.5	0.7	0.9	V_{PP}
CML Output Option ²	V.	2.5/3.3 V option mid-level	—	V _{DD} - 1.30		V
	V _O	1.8 V option mid-level	—	$V_{DD} - 0.36$		V
	V	2.5/3.3 V option swing (diff)	1.10	1.50	1.90	V _{PP}
	V _{OD}	1.8 V option swing (diff)	0.35	0.425	0.50	V _{PP}
CMOS Quitaut Option ³	V _{OH}	I _{OH} = 32 mA	0.8 x V _{DD}	_	V _{DD}	V
CMOS Output Option ³	V _{OL}	I _{OL} = 32 mA	—	_	0.4	V
	+ +	LVPECL/LVDS/CML	—	_	350	ps
Rise/Fall time (20/80%)	t _{R,} t _F	CMOS with $C_L = 15 \text{ pF}$	—	1	—	ns
Symmetry (duty cycle)	SYM	LVPECL: V _{DD} - 1.3 V (diff) LVDS: 1.25 V (diff) CMOS: V _{DD} /2	45	_	55	%
Notes: 1. R _{term} = 50 Ω to V _{DD} – 2. R _{term} = 100 Ω (different						

R_{term} = 100
 C_L = 15 pF



Table 5. CLK± Output Phase Jitter (Si570)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Phase Jitter (RMS) ¹	фJ	12 kHz to 20 MHz (OC-48)	_	0.25	0.40	ps
for $F_{OUT} \ge 500 \text{ MHz}$		50 kHz to 80 MHz (OC-192)	_	0.26	0.37	
Phase Jitter (RMS) ¹	фJ	12 kHz to 20 MHz (OC-48)	_	0.36	0.50	ps
for F _{OUT} of 125 to 500 MHz		50 kHz to 80 MHz (OC-192) ²	_	0.34	0.42	
Phase Jitter (RMS)	фJ	12 kHz to 20 MHz (OC-48) ²	_	0.62		ps
for F _{OUT} of 10 to 160 MHz CMOS Output Only		50 kHz to 20 MHz ²	_	0.61		
 Notes: 1. Refer to AN256 for further inf 2. Max offset frequencies: 80 MHz for FOUT ≥ 250 MHz 20 MHz for 50 MHz ≤ FOUT < 2 MHz for 10 MHz ≤ FOUT < 	2 <250 MHz					



Table 6. CLK± Output Phase Jitter (Si571)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Phase Jitter (RMS) ^{1,2,3}	фJ	Kv = 33 ppm/V				ps
for F _{OUT} ≥ 500 MHz		12 kHz to 20 MHz (OC-48)	—	0.26	—	
		50 kHz to 80 MHz (OC-192)	—	0.26	—	
		Kv = 45 ppm/V				
		12 kHz to 20 MHz (OC-48)	—	0.27	—	
		50 kHz to 80 MHz (OC-192)	—	0.26	—	
		Kv = 90 ppm/V				
		12 kHz to 20 MHz (OC-48)	—	0.32	—	
		50 kHz to 80 MHz (OC-192)	—	0.26	—	
		Kv = 135 ppm/V				
		12 kHz to 20 MHz (OC-48)	—	0.40	—	
		50 kHz to 80 MHz (OC-192)	—	0.27	—	
		Kv = 180 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	0.49	—	
		50 kHz to 80 MHz (OC-192)	—	0.28	—	
		Kv = 356 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	0.87	—	
		50 kHz to 80 MHz (OC-192)	—	0.33	—	
		CML. Refer to AN255, AN256, and A				

For best jitter and phase noise performance, always choose the smallest K_V that meets the application's minimum APR requirements. See "AN266: VCXO Tuning Slope (kV), Stability, and Absolute Pull Range (APR)" for more information.

- **3.** See "AN255: Replacing 622 MHz VCSO devices with the Si550 VCXO" for comparison highlighting power supply rejection (PSR) advantage of Si55x versus SAW-based solutions.
- 4. Single ended mode: CMOS. Refer to the following application notes for further information: "AN255: Replacing 622 MHz VCSO Devices with the Si55x VCXO" "AN256: Integrated Phase Noise" "AN266: VCXO Tuning Slope (kV), Stability, and Absolute Pull Range (APR)"
 5. May effect frequencies:
- $\begin{array}{ll} \text{5. Max offset frequencies:} \\ \text{80 MHz for } F_{\text{OUT}} \geq 250 \text{ MHz} \\ \text{20 MHz for 50 MHz} \leq F_{\text{OUT}} <\!\!250 \text{ MHz} \\ \text{2 MHz for 10 MHz} \leq F_{\text{OUT}} <\!\!50 \text{ MHz}. \end{array}$



Table 6. CLK± Output Phase Jitter (Si571) (Continued)

Symbol	Test Condition	Min	Тур	Max	Unit
φJ	Kv = 33 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		0.63 0.62		ps
	Kv = 45 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		0.63 0.62		
	Kv = 90 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		0.67 0.66		
	Kv = 135 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		0.74 0.72		
	Kv = 180 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		0.83 0.8		
	Kv = 356 ppm/V 12 kHz to 20 MHz (OC-48) 50 kHz to 20 MHz		1.26 1.2		
	-		φ _J Kv = 33 ppm/V		$ \begin{split} \varphi_J & \begin{array}{c} Kv = 33 \ \text{ppm/V} & & & & & & & & & & & & & & & & & & &$

requirements. See "AN266: VCXO Tuning Slope (kV), Stability, and Absolute Pull Range (APR)" for more information.

3. See "AN255: Replacing 622 MHz VCSO devices with the Si550 VCXO" for comparison highlighting power supply rejection (PSR) advantage of Si55x versus SAW-based solutions.

4. Single ended mode: CMOS. Refer to the following application notes for further information: "AN255: Replacing 622 MHz VCSO Devices with the Si55x VCXO" "AN256: Integrated Phase Noise" "AN266: VCXO Tuning Slope (kV), Stability, and Absolute Pull Range (APR)" 5. Max offset frequencies:

80 MHz for $F_{OUT} \ge 250$ MHz 20 MHz for 50 MHz $\le F_{OUT} < 250$ MHz 2 MHz for 10 MHz \leq F_{OUT} <50 MHz.



Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Phase Jitter (RMS) ^{1,2,3,5}	фJ	Kv = 33 ppm/V				ps
for F _{OUT} of 125 to		12 kHz to 20 MHz (OC-48)	_	0.37	—	-
500 MHz		50 kHz to 80 MHz (OC-192)	_	0.33	—	
		Kv = 45 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	0.37	—	
		50 kHz to 80 MHz (OC-192)		0.33	—	
		Kv = 90 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	0.43	—	
		50 kHz to 80 MHz (OC-192)	_	0.34	—	-
		Kv = 135 ppm/V				
		12 kHz to 20 MHz (OC-48)	—	0.50	—	
		50 kHz to 80 MHz (OC-192)	_	0.34	—	
		Kv = 180 ppm/V				
		12 kHz to 20 MHz (OC-48)		0.59	—	
		50 kHz to 80 MHz (OC-192)	—	0.35	—	
		Kv = 356 ppm/V				
		12 kHz to 20 MHz (OC-48)	_	1.00	—	
		50 kHz to 80 MHz (OC-192)	—	0.39	—	
		CML. Refer to AN255, AN256, and A prmance, always choose the smallest				

See "AN255: Replacing 622 MHz VCSO devices with the Si550 VCXO" for comparison highlighting power supply rejection (PSR) advantage of Si55x versus SAW-based solutions.

4.	Single ended mode: CMOS. Refer to the following application notes for further information:
	"AN255: Replacing 622 MHz VCSO Devices with the Si55x VCXO"
	"AN256: Integrated Phase Noise"
	"AN266: VCXO Tuning Slope (kV), Stability, and Absolute Pull Range (APR)"
5.	Max offset frequencies:

80 MHz for F_{OUT} ≥ 250 MHz 20 MHz for 50 MHz ≤ F_{OUT} <250 MHz 2 MHz for 10 MHz ≤ F_{OUT} <50 MHz.

Table 7. CLK± Output Period Jitter

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Pariad littar*	I	RMS	_	2	—	nc
Period Jitter*	JPER	Peak-to-Peak	_	14	—	ps
*Note: Any output mode, including CMOS, LVPECL, LVDS, CML. N = 1000 cycles. Refer to "AN279: Estimating Period Jitter from Phase Noise" for further information.						



Offset Frequency (f)	120.00 MHz LVDS	156.25 MHz LVPECL	622.08 MHz LVPECL	Unit
100 Hz	-112	-105	-97	
1 kHz	-122	-122	-107	
10 kHz	-132	-128	-116	
100 kHz	-137	-135	-121	dBc/Hz
1 MHz	-144	-144	-134	
10 MHz	-150	-147	-146	
100 MHz	n/a	n/a	-148	

Table 9. Typical CLK± Output Phase Noise (Si571)

Offset Frequency (f)	74.25 MHz 90 ppm/V LVPECL	491.52 MHz 45 ppm/V LVPECL	622.08 MHz 135 ppm/V LVPECL	Unit
100 Hz	-87	-75	65	dBc/Hz
1 kHz	-114	-100	90	
10 kHz	-132	-116	109	
100 kHz	-142	-124	121	
1 MHz	-148	-135	134	
10 MHz	-150	-146	146	
100 MHz	n/a	-147	147	

Table 10. Environmental Compliance(The Si570/571 meets the following qualification test requirements.)

Parameter	Conditions/Test Method
Mechanical Shock	MIL-STD-883, Method 2002
Mechanical Vibration	MIL-STD-883, Method 2007
Solderability	MIL-STD-883, Method 2003
Gross and Fine Leak	MIL-STD-883, Method 1014
Resistance to Solder Heat	MIL-STD-883, Method 2036
Moisture Sensitivity Level	J-STD-020, MSL1
Contact Pads	Gold over Nickel



Table 11. Programming Constraints and Timing (V_{DD} = 3.3 V $\pm 10\%,~T_A$ = -40 to 85 $^{\circ}C)$

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
		$HS_DIV \times N1 > = 6$	10	—	945	MHz
Output Frequency Range	CKO _F	HS_DIV = 5 N1 = 1	970	_	1134	MHz
		HS_DIV = 4 N1 = 1	1.2125	_	1.4175	GHz
Frequency Reprogramming Resolution	M _{RES}	f _{xtal} = 114.285 MHz	—	0.09	—	ppb
Internal Oscillator Frequency	fosc		4850	—	5670	MHz
Internal Crystal Frequency Accuracy	f _{XTAL}	Maximum variation is ±2000 ppm	—	114.285	—	MHz
Delta Frequency for Continuous Output		From center frequency	-3500	—	+3500	ppm
Unfreeze to NewFreq Timeout			_	—	10	ms
Settling Time for Small Frequency Change		<±3500 ppm from center frequency	_	—	100	μs
Settling Time for Large Frequency Change		>±3500 ppm from center frequency after setting NewFreq bit	_	—	10	ms

Table 12. Thermal Characteristics

(Typical values TA = 25 $^{\circ}C,~V_{DD}$ = 3.3 V)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Thermal Resistance Junction to Ambient	θ_{JA}	Still Air	_	84.6	_	°C/W
Thermal Resistance Junction to Case	θ_{JC}	Still Air	_	38.8	_	°C/W
Ambient Temperature	T _A		-40	_	85	°C
Junction Temperature	Т _Ј				125	°C



Table 13. Absolute Maximum Ratings^{1,2}

Parameter	Symbol	Rating	Unit	
Supply Voltage, 1.8 V Option	V_{DD}	-0.5 to +1.9	V	
Supply Voltage, 2.5/3.3 V Option	V _{DD}	-0.5 to +3.8	V	
Input Voltage	VI	-0.5 to V _{DD} + 0.3	V	
Storage Temperature	Τ _S	-55 to +125	°C	
ESD Sensitivity (HBM, per JESD22-A114)	ESD	>2000	V	
Soldering Temperature (Lead-free Profile)	T _{PEAK}	260	°C	
Soldering Temperature Time @ T _{PEAK} (Lead-free Profile)	t _P	20–40	seconds	
Netes				

Notes:

1. Stresses beyond the absolute maximum ratings may cause permanent damage to the device. Functional operation or specification compliance is not implied at these conditions.

2. The device is compliant with JEDEC J-STD-020. Refer to packaging FAQ available for download at www.siliconlabs.com/VCXO for further information, including soldering profiles.



3. Functional Description

The Si570 XO and the Si571 VCXO are low-jitter oscillators ideally suited for applications requiring programmable frequencies. The Si57x can be programmed to generate virtually any output clock in the range of 10 MHz to 1.4 GHz. Output jitter performance complies with and exceeds the strict requirements of high-speed communication systems including OC-192/STM-64 and 10 Gigabit Ethernet (10 GbE).

The Si57x consists of a digitally-controlled oscillator (DCO) based on Silicon Laboratories' third-generation DSPLL technology, which is driven by an internal fixed-frequency crystal reference.

The device's default output frequency is set at the factory and can be reprogrammed through the two-wire I^2C serial port. Once the device is powered down, it will return to its factory-set default output frequency.

While the Si570 outputs a fixed frequency, the Si571 has a pullable output frequency using the voltage control input pin. This makes the Si571 an ideal choice for high-performance, low-jitter, phase-locked loops.

3.1. Programming a New Output Frequency

The output frequency (f_{out}) is determined by programming the DCO frequency (f_{DCO}) and the device's output dividers (HS_DIV, N1). The output frequency is calculated using the following equation:

$$f_{out} = \frac{f_{DCO}}{Output \text{ Dividers}} = \frac{f_{XTAL} \times RFREQ}{HSDIV \times N1}$$

The DCO frequency is adjustable in the range of 4.85 to 5.67 GHz by setting the high-resolution 38-bit fractional multiplier (RFREQ). The DCO frequency is the product of the internal fixed-frequency crystal (f_{XTAL}) and RFREQ.

The 38-bit resolution of RFREQ allows the DCO frequency to have a programmable frequency resolution of 0.09 ppb.

As shown in Figure 3, the device allows reprogramming of the DCO frequency up to ± 3500 ppm from the center frequency configuration without interruption to the output clock. Changes greater than the ± 3500 ppm window will cause the device to recalibrate its internal tuning circuitry, forcing the output clock to momentarily stop and start at any arbitrary point during a clock cycle. This re-calibration process establishes a new center frequency and can take up to 10 ms. Circuitry receiving a clock from the Si57x device that is sensitive to glitches or runt pulses may have to be reset once the recalibration process is complete.

3.1.1. Reconfiguring the Output Clock for a Small Change in Frequency

For output changes less than ± 3500 ppm from the center frequency configuration, the DCO frequency is the only value that needs reprogramming. Since $f_{DCO} = f_{XTAL} \times RFREQ$, and that f_{XTAL} is fixed, changing the DCO frequency is as simple as reconfiguring the RFREQ value as outlined below:

- Using the serial port, read the current RFREQ value (addresses 7–12 for all Si571 devices and Si570 devices with 20 ppm and 50 ppm temperature stability; or addresses 13–18 for Si570 devices with 7 ppm temperature stability).
- 2. Calculate the new value of RFREQ given the change in frequency.

$$RFREQ_{new} = RFREQ_{current} \times \frac{f_{out_new}}{f_{out_current}}$$

3. Using the serial port, write the new RFREQ value (addresses 7–12 for all Si571 devices and Si570 devices with 20 ppm and 50 ppm temperature stability; or addresses 13–18 for Si570 devices with 7 ppm temperature stability).

Example:

An Si570 generating a 148.35 MHz clock must be reconfigured "on-the-fly" to generate a 148.5 MHz clock. This represents a change of +1011.122 ppm, which is well within the \pm 3500 ppm window.

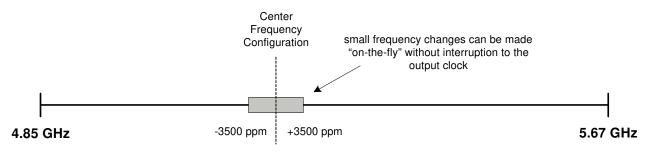


Figure 3. DCO Frequency Range



A typical frequency configuration for this example:

RFREQ_{current} = 0x2EBB04CE0

F_{out_current} = 148.35 MHz

 $F_{out new} = 148.50 \text{ MHz}$

Calculate RFREQ_{new} to change the output frequency from 148.35 MHz to 148.5 MHz:

$$RFREQ_{new} = 0x2EBB04CE0 \times \frac{148.50 \text{ MHz}}{148.35 \text{ MHz}}$$

= 0x2EC71D666

Note: Performing calculations with RFREQ requires a minimum of 38-bit arithmetic precision.

Even relatively small changes in output frequency may require writing more than 1 RFREQ register. Such multiregister RFREQ writes can impact the output clock frequency on a register-by-register basis during updating.

Interim changes to the output clock during RFREQ writes can be prevented by using the following procedure:

1. Freeze the "M" value (Set Register 135 bit 5 = 1).

2. Write the new frequency configuration (RFREQ).

3. Unfreeze the "M" value (Set Register 135 bit 5 = 0)

3.1.2. Reconfiguring the Output Clock for Large Changes in Output Frequency

For output frequency changes outside of ± 3500 ppm from the center frequency, it is likely that both the DCO frequency and the output dividers need to be reprogrammed. Note that changing the DCO frequency outside of the ± 3500 ppm window will cause the output to momentarily stop and restart at any arbitrary point in a clock cycle. Devices sensitive to glitches or runt pulses may have to be reset once reconfiguration is complete.

The process for reconfiguring the output frequency outside of a ±3500 ppm window first requires reading the current RFREQ, HSDIV, and N1 values. Next, calculate fXTAL for the device. Note that, due to slight variations of the internal crystal frequency from one device to another, each device may have a different RFREQ value or possibly even different HSDIV or N1 values to maintain the same output frequency. It is necessary to calculate fXTAL for each device. Third, write the new values back to the device using the appropriate registers (addresses 7-12 for all Si571 devices and Si570 devices with 20 ppm and 50 ppm temperature stability; or addresses 13-18 for Si570 devices with 7 ppm temperature stability) sequencing as described in "3.1.2.1.Writing the New Frequency Configuration".

$$f_{XTAL} = \frac{F_{out} \times HSDIV \times N1}{RFREQ}$$

Once f_{XTAL} has been determined, new values for RFREQ, HSDIV, and N1 are calculated to generate a new output frequency (f_{out_new}). New values can be calculated manually or with the Si57x-EVB software, which provides a user-friendly application to help find the optimum values.

The first step in manually calculating the frequency configuration is to determine new frequency divider values (HSDIV, N1). Given the desired output frequency (fout_new), find the frequency divider values that will keep the DCO oscillation frequency in the range of 4.85 to 5.67 GHz.

$$f_{DCO_new} = f_{out_new} \times HSDIV_{new} \times N1_{new}$$

Valid values of HSDIV are 4, 5, 6, 7, 9 or 11. N1 can be selected as 1 or any even number up to 128 (i.e. 1, 2, 4, 6, 8, 10 ... 128). To help minimize the device's power consumption, the divider values should be selected to keep the DCO's oscillation frequency as low as possible. The lowest value of N1 with the highest value of HS_DIV also results in the best power savings.

Once HS_DIV and N1 have been determined, the next step is to calculate the reference frequency multiplier (RFREQ).

$$\mathsf{RFREQ}_{\mathsf{new}} = \frac{\mathsf{f}_{\mathsf{DCO_new}}}{\mathsf{f}_{\mathsf{XTAL}}}$$

RFREQ is programmable as a 38-bit binary fractional frequency multiplier with the first 10 most significant bits (MSBs) representing the integer portion of the multiplier, and the 28 least significant bits (LSBs) representing the fractional portion.

Before entering a fractional number into the RFREQ register, it must be converted to a 38-bit integer using a bitwise left shift operation by 28 bits, which effectively multiplies RFREQ by 2^{28} .

Example:

RFREQ = 46.043042064d

Multiply RFREQ by 2²⁸ = 12359584992.1

Discard the fractional portion = 12359584992

Convert to hexadecimal = 02E0B04CE0h

In the example above, the multiplication operation requires 38-bit precision. If 38-bit arithmetic precision is not available, then the fractional portion can be separated from the integer and shifted to the left by 28-bits. The result is concatenated with the integer portion



to form a full 38-bit word. An example of this operation is shown in Figure 4.

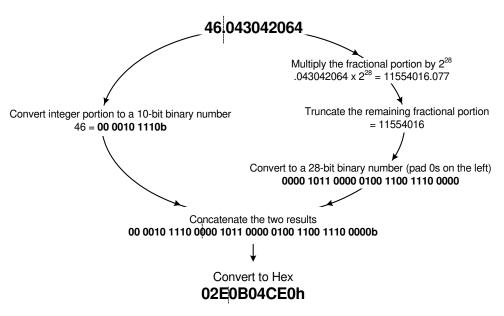


Figure 4. Example of RFREQ Decimal to Hexadecimal Conversion

3.1.2.1. Writing the New Frequency Configuration

Once the new values for RFREQ, HSDIV, and N1 are determined, they can be written directly into the device from the serial port using the following procedure:

- 1. Freeze the DCO (bit 4 of Register 137)
- Write the new frequency configuration (RFREQ, HSDIV, and N1) to addresses 7–12 for all Si571 devices and Si570 devices with 20 ppm and 50 ppm temperature stability; or addresses 13–18 for Si570 devices with 7 ppm temperature stability.
- 3. Unfreeze the DCO and assert the NewFreq bit (bit 6 of Register 135) within the maximum Unfreeze to NewFreq Timeout specified in Table 11, "Programming Constraints and Timing," on page 13.

The process of freezing and unfreezing the DCO will cause the output clock to momentarily stop and start at any arbitrary point during a clock cycle. This process can take up to 10 ms. Circuitry that is sensitive to glitches or runt pulses may have to be reset after the new frequency configuration is written.

Example:

An Si570 generating 156.25 MHz must be re-configured to generate a 161.1328125 MHz clock (156.25 MHz x 66/ 64). This frequency change is greater than ±3500 ppm.

f_{out} = 156.25 MHz

Read the current values for RFREQ, HS_DIV, N1:

RFREQ_{current} = 0x2BC011EB8h = 11744124600d, 11744124600d x 2²⁸ = 43.7502734363d HS DIV = 4

N1 = 8

Calculate f_{XTAL}, f_{DCO_current}

 $f_{DCO \ current} = f_{out} \times HSDV \times N1 = 5.00000000 \text{ GHz}$

 $f_{XTAL} = \frac{f_{DCO_current}}{RFREQ_{current}} = 114.285 \text{ MHz}$



Given $f_{out_new} = 161.1328125$ MHz, choose output dividers that will keep f_{DCO} within the range of 4.85 to 5.67 GHz. In this case, keeping the same output dividers will still keep f_{DCO} within its range limits:

 $f_{DCO_new} = f_{out_new} \times HSDV_{new} \times N1_{new}$ = 161.1328125 MHz × 4 × 8 = 5.156250000 GHz

Calculate the new value of RFREQ given the new DCO frequency:

 $RFREQ_{new} = \frac{f_{DCO_new}}{f_{XTAL}} = 45.11746948$ = 0x2D1E127AD



3.2. Si570 Programming Procedure

This following example was generated using *Si514/70/71/98/99 Programmable Oscillator Software* V4.0.1 found under the **Tools** tab at the following web page.

http://www.siliconlabs.com/products/clocksoscillators/oscillators/Pages/i2c-oscillator.aspx

On that same web page, the AN334 Si57x I2C XO/VCXO ANSI C Reference Design contains example C code for calculating register settings on the fly.

1. Read start-up frequency configuration (RFREQ, HS_DIV, and N1) from the device after power-up or register reset.

```
Registers for the Current Configuration
 Register
            Data
     7
              0x01
     8
              0xC2
     9
              0xBC
    10
              0x01
    11
              0x1E
    12
              0xB8
RFREO = 0x2BC011EB8
        = 0x2BC011EB8 / (2^{28}) = 43.75027344
 HS_DIV = 0x0 = 4
        = 0x7 = 8
 Ν1
```

2. Calculate the actual nominal crystal frequency where f0 is the start-up output frequency.

fxtal = (f0 x HS_DIV x N1) / RFREQ
= (156.25000000 MHz x 4 x 8) / 43.750273436
= 114.285000000 MHz

3. Choose the new output frequency (f1).

Output Frequency (f1) = 161.132812000 MHz

4. Choose the output dividers for the new frequency configuration (HS_DIV and N1) by ensuring the DCO oscillation frequency (fdco) is between 4.85 GHz and 5.67 GHz where fdco = f1 x HS_DIV x N1. See the Divider Combinations tab for more options.

```
HS_DIV = 0x0 = 4
N1 = 0x7 = 8
fdco = f1 x HS_DIV x N1
= 161.132812000 MHz x 4 x 8
= 5.156249984 GHz
```



Si570/Si571

5. Calculate the new crystal frequency multiplication ratio (RFREQ) as RFREQ = fdco / fxtal

```
RFREQ = fdco / fxtal
= 5.156249984 GHz / 114.285000000 MHz
= 45.11746934
= 45.11746934 x (2^28) = 0x2D1E12788
```

- 6. Freeze the DCO by setting Freeze DCO = 1 (bit 4 of register 137).
- 7. Write the new frequency configuration (RFREQ, HS_DIV, and N1)

```
Registers for the New Configuration
Register Data
7 0x01
8 0xC2
9 0xD1
10 0xE1
11 0x27
12 0x88
```

8. Unfreeze the DCO by setting Freeze DCO = 0 and assert the NewFreq bit (bit 6 of register 135) within 10 ms.



3.3. Si570 Troubleshooting FAQ

1. Is the I²C bus working correctly and using the correct I²C address?

Probing the device I^2C pins with an oscilloscope can sometimes reveal signal integrity problems. Si570/Si571 I^2C communication is normally very robust, so if other devices on the I^2C bus are communicating successfully, then the Si570/Si571 should also work.

You can confirm the specific I²C address expected by an Si570/Si571 device by using the part number lookup utility available on the Silicon Laboratories web site.

http://www.silabs.com/custom-timing

2. Is the correct register bank being written based on device stability?

Si570/Si571 devices use different configuration registers for 7 ppm temperature stability devices than they do for 20 ppm or 50 ppm temperature stability devices. The temperature stability of a Si570/Si571 device can be confirmed using the part number lookup utility available on the Silicon Laboratories web site or by referencing the 2nd ordering option code in the part number.

http://www.silabs.com/custom-timing

2nd Ordering Option Code:

A : 50 ppm temperature stability, 61.5 ppm total stability => Configuration Registers 7-12

B : 20 ppm temperature stability, 31.5 ppm total stability => Configuration Registers 7-12

C : 7 ppm temperature stability, 20 ppm total stability => Configuration Registers 13-18

3. Is the part-to-part variation in FXTAL included in calculations?

It is required that one determine the internal crystal frequency for each individual part before calculating a new output frequency. The procedure for determining the internal crystal frequency from the register values of a device is described elsewhere in this data sheet. See Section 3.2.

FXTAL = (FOUT x HSDIV x N1) / RFREQ <= note that RFREQ used here is the register value divided by 2^{28}

It is a common error to calculate the internal crystal frequency for one device and then use that same crystal frequency for all later devices. This will lead to offset errors in the output frequency accuracy from part-to-part. The internal crystal frequency must be calculated for each individual device.

4. Is the Unfreeze to NewFreq timeout spec being exceeded?

The Si570/Si571 requires the DCO to be 'frozen' when changing register values and then 'unfrozen' and a calibration initiated by writing the 'NewFreq' bit to restart it properly. If the 'unfreeze' and 'NewFreq' writes are delayed by 10 ms or more, the internal state machine can timeout and cause the configuration to revert to default values.

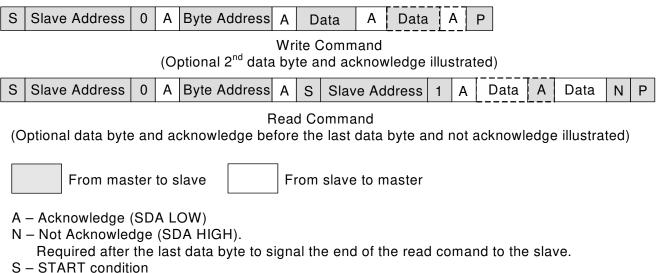
This 'unfreeze' and 'NewFreq' timing requirement is not usually a problem since the writes are done back-to-back, but if there is an interrupt or other system delay that may cause this 10 ms timing to be exceeded, it should be considered as a possible source of issues reprogramming the Si570/Si571.



3.4. I²C Interface

The control interface to the Si570 is an I^2 C-compatible 2-wire bus for bidirectional communication. The bus consists of a bidirectional serial data line (SDA) and a serial clock input (SCL). Both lines must be connected to the positive supply via an external pullup. Fast mode operation is supported for transfer rates up to 400 kbps as specified in the I^2 C-Bus Specification standard.

Figure 5 shows the command format for both read and write access. Data is always sent MSB. Data length is 1 byte. Read and write commands support 1 or more data bytes as illustrated. The master must send a Not Acknowledge and a Stop after the last read data byte to terminate the read command. The timing specifications and timing diagram for the I²C bus can be found in the I²C-Bus Specification standard (fast mode operation). The device I²C address is specified in the part number.



P – STOP condition

Figure 5. I²C Command Format



4. Serial Port Registers

Note: Any register not listed here is reserved and must not be written. All bits are R/W unless otherwise noted.

Register	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	
7	High Speed/ N1 Dividers	ŀ	HS_DIV[2:0] N1[6:2]						1	
8	Reference Frequency	N1[1:0]		RFREQ[37:32]					
9	Reference Frequency		RFREQ[31:24]							
10	Reference Frequency				RFREG	RFREQ[23:16]				
11	Reference Frequency		RFREQ[15:8]							
12	Reference Frequency		RFREQ[7:0]							
13	High Speed/ N1 Dividers	HS_DIV_7PPM[2:0]			N1_7PPM[6:2]					
14	Reference Frequency	N1_7PI	PM[1:0]		RFREQ_7PPM[37:32]					
15	Reference Frequency			I	RFREQ_7F	PPM[31:24]				
16	Reference Frequency			I	RFREQ_7F	PPM[23:16]				
17	Reference Frequency		RFREQ_7PPM[15:8]							
18	Reference Frequency		RFREQ_7PPM[7:0]							
135	Reset/Freeze/ Memory Control	RST_REG	NewFreq	Freeze M	Freeze VCADC				RECALL	
137	Freeze DCO				Freeze DCO					



Register 7. High Speed/N1 Dividers

Bit	D7	D6	D5	D4	D3	D2	D1	D0
ы	07	Do	05	D4	03	DZ	וט	DU
Name	ŀ	HS_DIV[2:0]				N1[6:2]		
Туре		R/W		·		R/W		
Bit	Name	Name Function						
7:5	HS_DIV[2:0]	Sets value 000 = 4 001 = 5 010 = 6 011 = 7 100 = Not 101 = 9	001 = 5 010 = 6 011 = 7 100 = Not used. 101 = 9 110 = Not used.					
4:0	N1[6:2]							or the N1 reg-

Register 8. Reference Frequency

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name	N1[1:0]	:0] RFREQ[37:32]					
Туре	ype R/W R/W							

Bit	Name	Function
7:6	N1[1:0]	CLKOUT Output Divider.
		Sets value for CLKOUT output divider. Allowed values are $[1, 2, 4, 6,, 2^7]$. Illegal odd divider values will be rounded up to the nearest even value. The value for the N1 register can be calculated by taking the divider ratio minus one. For example, to divide by 10, write 0001001 (9 decimal) to the N1 registers. 0000000 = 1 1111111 = 2 ⁷
5:0	RFREQ[37:32]	Reference Frequency.
		Frequency control input to DCO.



Register 9. Reference Frequency

Bit	D7	D6	D5	D4	D3	D2	D1	D0	
Name	RFREQ[31:24]								
Туре	R/W								
Bit	Name		Function						
7:0	RFREQ[31:2	-	Reference Frequency. Frequency control input to DCO.						

Register 10. Reference Frequency

Bit	Bit D7 D6 D5 D4 D3 D2					D2	D1	D0		
Name	•	RFREQ[23:16]								
Туре	R/W									
Bit	Name		Function							
7:0	RFREQ[23:1	-	Reference Frequency. Frequency control input to DCO.							

Register 11. Reference Frequency

Bit	D7	D6	D5	D4	D3	D2	D1	D0		
Name	RFREQ[15:8]									
Туре	R/W									
Bit	Name	e Function								
7:0	RFREQ[15:8	Reference Frequency. Frequency control input to DCO.								

